

1.2V Drive Nch MOSFET

RUM002N05

Structure

Silicon N-channel MOSFET

Features

High speed switing.
Small package(VMT3).
Ultra low voltage drive(1.2V drive).

Application

Switching

Packaging specifications

Туре	Package	Taping
	Code	T2L
	Basic ordering unit (pieces)	8000
RUM002N0)5	0

• Absolute maximum ratings (Ta = 25°C)

		/		
Para	meter	Symbol	Limits	Unit
Drain-source voltage	;	V _{DSS}	50	V
Gate-source voltage		V _{GSS}	±8	V
Drain current	Continuous	I _D	±200	mA
Dialit current	Pulsed	I _{DP} *1	±800	mA
Source current	Continuous	I _S	125	mA
(Body Diode)	Pulsed	I _{SP} *1	800	mA
Power dissipation		P _D *2	P _D ^{*2} 150	
Channel temperature	9	Tch	150	°C
Range of storage ter	nperature	Tstg	-55 to +150	°C

*1 Pw≤10 μ s, Duty cycle≤1%

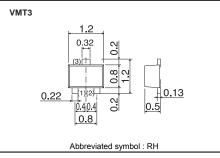
*2 Each terminal mounted on a recommended land.

Thermal resistance

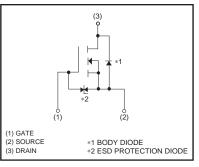
Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	833	°C / W

* Each terminal mounted on a recommended land.

• Dimensions (Unit : mm)



Inner circuit



•Electrical characteristics (Ta = 25°C)

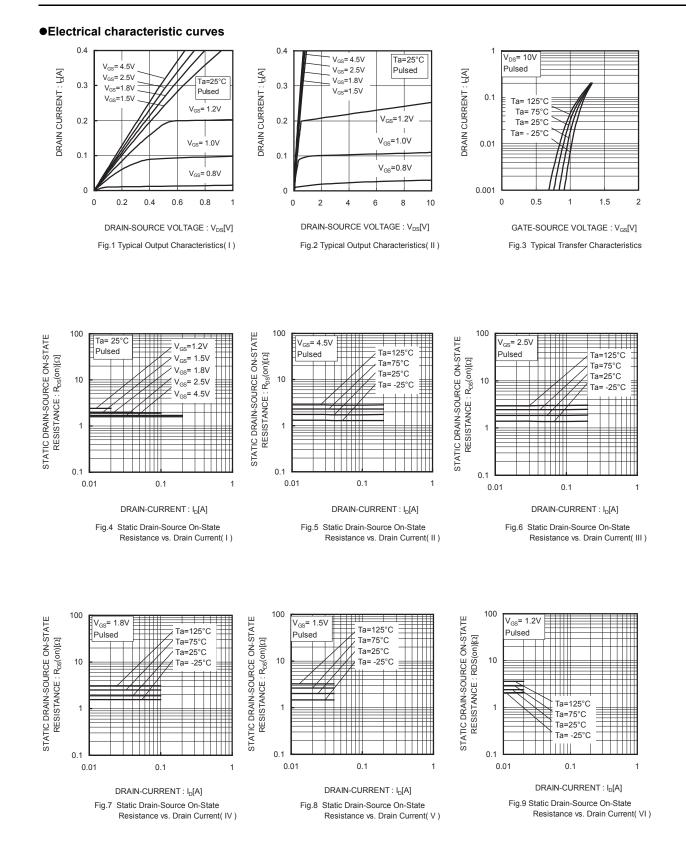
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	-	-	±10	μA	V _{GS} =±8V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR)DSS}	50	-	-	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	-	-	1	μA	V _{DS} =50V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	0.3	-	1.0	V	V _{DS} =10V, I _D =1mA
		-	1.6	2.2		I _D =200mA, V _{GS} =4.5V
		-	1.7	2.4		I _D =200mA, V _{GS} =2.5V
Static drain-source on-state resistance	R _{DS (on)} *	-	1.9	2.7	Ω	I _D =100mA, V _{GS} =1.8V
		-	2.0	4.0		I _D =40mA, V _{GS} =1.5V
		-	2.4	7.2		I _D =20mA, V _{GS} =1.2V
Forward transfer admittance	۱۲ _{fs} ۱*	0.4	-	-	S	I _D =200mA, V _{DS} =10V
Input capacitance	C _{iss}	-	25	-	pF	V _{DS} =10V
Output capacitance	C _{oss}	-	6	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	-	3	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	-	4	-	ns	I _D =100mA, V _{DD} ≒30V
Rise time	t _r *	-	6	-	ns	V _{GS} =4.5V
Turn-off delay time	t _{d(off)} *	-	15	-	ns	R _L =300Ω
Fall time	t _f *	-	55	-	ns	R _G =10Ω

*Pulsed

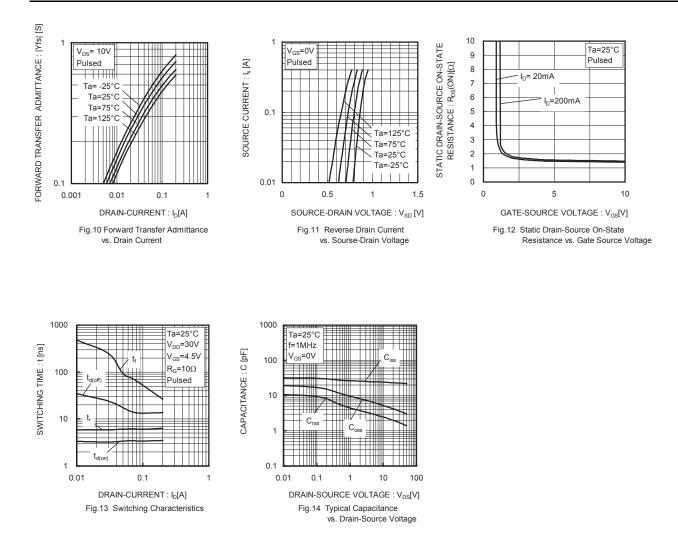
•Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V_{SD}^{*}	-	-	1.2	V	I _s =200mA, V _{GS} =0V

*Pulsed



RUM002N05



Measurement circuits

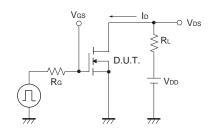


Fig.1-1 Switching time measurement circuit

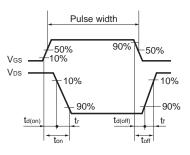


Fig.1-2 Switching waveforms

Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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